

1. (twice amended) A capacitor fabrication method comprising:
 - forming a first capacitor electrode comprising TiN over a substrate, the first electrode having an innermost surface area per unit area and an outermost surface area per unit area that are both greater than an outer surface area per unit area of the substrate;
 - forming a capacitor dielectric layer over the first electrode; and
 - forming a second capacitor electrode over the dielectric layer.
7. (once amended) The method of claim 1 wherein the outermost surface area of the first electrode is at least 30% greater than the outer surface area of the substrate.

10. (once amended) A capacitor fabrication method comprising:
 - forming an opening in an insulative layer over a substrate, the opening having sides and a bottom;
 - forming a layer of polysilicon over the sides and bottom of the opening;
 - removing the polysilicon layer from over the bottom of the opening;
 - converting at least some of the polysilicon layer to hemispherical grain polysilicon;
 - conformally forming a first capacitor electrode on the hemispherical grain polysilicon, the first electrode being sufficiently thin that the first electrode has an outermost surface area per unit area greater than an outer surface area per unit area of the substrate underlying the first electrode;
 - forming a capacitor dielectric layer on the first electrode; and
 - forming a second capacitor electrode over the dielectric layer.